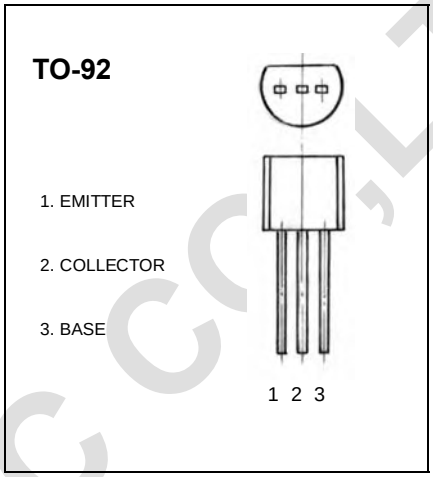
2SA836 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.2 W (Tamb=25℃)

Collector current

I_{CM}: -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -55 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -10μA , I_E=0	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1 mA , I_B=0	-55			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-18V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -2V , I_C=0			-0.05	μA
DC current gain	h_{FE}	V_{CE}=-12 V, I_C= -2mA	160		500	
Collector-emitter saturation voltage	V_{CEsat}	I_C= -10mA, I_B= -1mA			-0.5	V
Base-emitter voltage	V_{BE}(ON)	V_{CE}=-12 V, I_C= -2mA			-0.75	V
Transition frequency	f_T	V_{CE}=-12 V, I_C= -2mA	150			MHz
Output capacitance	C_{ob}	V_{CE}=-10V, I_E=0,f=1 MHz			4	pF
Noise figure	NF	V_{CE}=-6V, I_C=0.1 mA, f=1 0Hz, R_G=10KΩ			5	dB
		V_{CE}=-6V, I_C=0.1 mA, f=1 kHz, R_G=10KΩ			1	

CLASSIFICATION OF h_{FE}

Rank	C	D
Range	160-320	250-500